

## Dual N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
40	0.027 at $V_{GS} = 10$ V	6.0	9.6
	0.032 at $V_{GS} = 4.5$ V	4.8	

### FEATURES

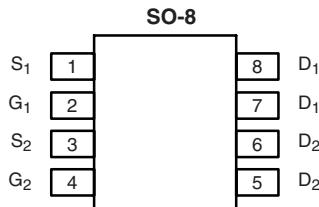
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 %  $R_g$  and UIS Tested



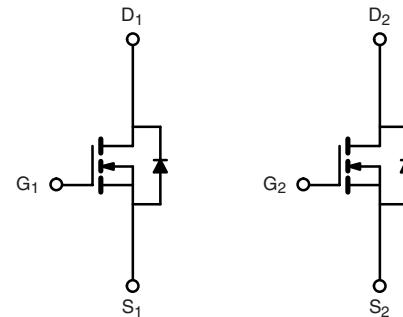
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- CCFL Inverter



Top View



N-Channel MOSFET

N-Channel MOSFET

**Ordering Information:** Si4910DY-T1-E3 (Lead (Pb)-free)  
Si4910DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 16$	
Continuous Drain Current ( $T_J = 150$ °C)	$T_C = 25$ °C	7.6	
	$T_C = 70$ °C	6.0	
	$T_A = 25$ °C	6.0 <sup>b, c</sup>	
	$T_A = 70$ °C	4.8 <sup>b, c</sup>	
Pulsed Drain Current (10 $\mu$ s Pulse Width)	$I_{DM}$	20	A
Source-Drain Current Diode Current	$T_C = 25$ °C	2.6	
	$T_A = 25$ °C	1.6 <sup>b, c</sup>	
Pulsed Source-Drain Current	$I_{SM}$	20	
Single Pulse Avalanche Current	$I_{AS}$	10	
Single Pulse Avalanche Energy	$E_{AS}$	5	
Maximum Power Dissipation	$T_C = 25$ °C	3.1	
	$T_C = 70$ °C	2	
	$T_A = 25$ °C	2 <sup>b, c</sup>	
	$T_A = 70$ °C	1.28 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	49	62.5	°C/W	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	30	40		

Notes:

- a. Based on  $T_C = 25$  °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c.  $t = 10$  s.
- d. Maximum under steady state conditions is 120 °C/W.

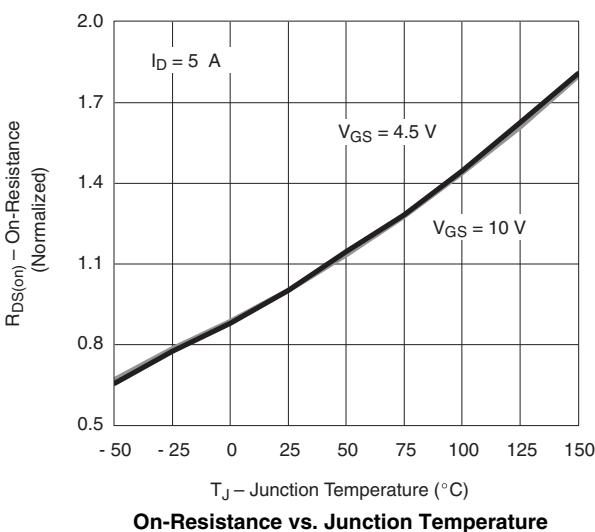
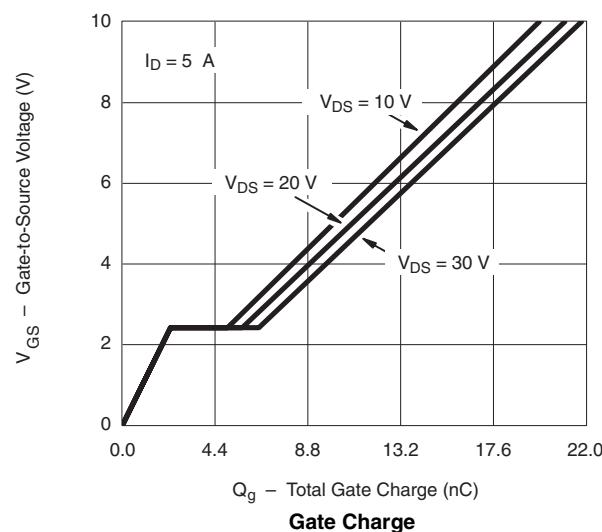
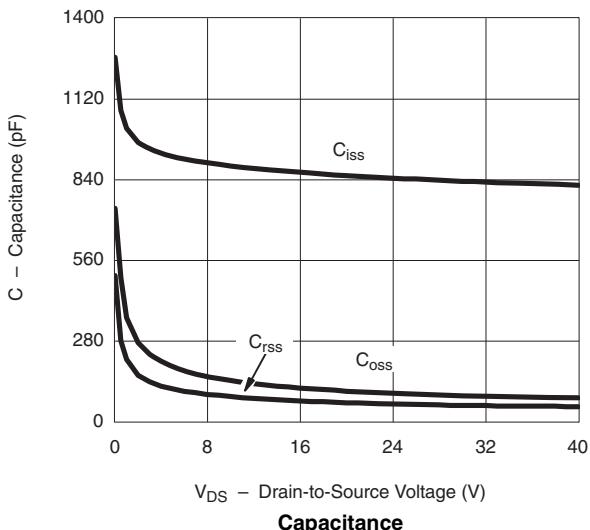
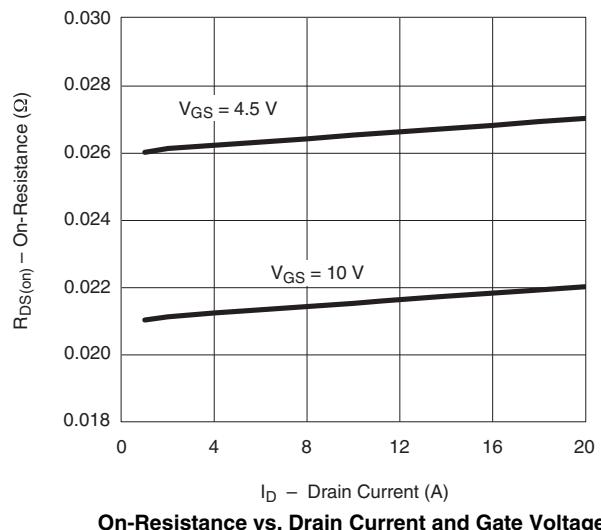
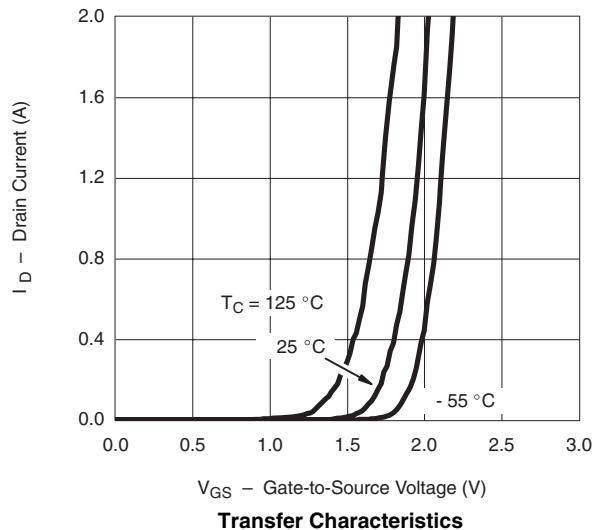
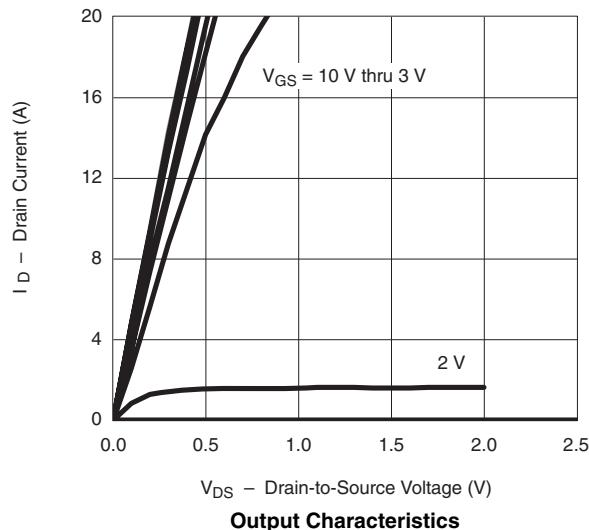
**SPECIFICATIONS**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		37		mV/ $^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 5		
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	0.6		2.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 16 \text{ V}$			100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40 \text{ V}$ , $V_{GS} = 0 \text{ V}$		1		$\mu\text{A}$
		$V_{DS} = 40 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$		10		
On-State Drain Current <sup>b</sup>	$I_{D(\text{on})}$	$V_{DS} = 5 \text{ V}$ , $V_{GS} = 10 \text{ V}$	20			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 6 \text{ A}$		0.022	0.027	$\Omega$
		$V_{GS} = 4.5 \text{ V}$ , $I_D = 4.8 \text{ A}$		0.026	0.032	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 6 \text{ A}$		20		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $I_D = 1 \text{ MHz}$		855		pF
Output Capacitance	$C_{oss}$			105		
Reverse Transfer Capacitance	$C_{rss}$			65		
Total Gate Charge	$Q_g$	$V_{DS} = 20 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 5 \text{ A}$		21	32	nC
				9.6	14.5	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 20 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 5 \text{ A}$		2.3		
Gate-Drain Charge	$Q_{gd}$			3.2		
Gate Resistance	$R_g$	$f = 1 \text{ MHz}$		2.5	3.8	$\Omega$
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 20 \text{ V}$ , $R_L = 4 \Omega$ $I_D \approx 5 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$		6	12	ns
Rise Time	$t_r$			11	20	
Turn-Off Delay Time	$t_{d(\text{off})}$			24	36	
Fall Time	$t_f$			6	12	
Turn-On Delay Time	$t_{d(\text{on})}$			12	20	
Rise Time	$t_r$	$V_{DD} = 20 \text{ V}$ , $R_L = 4 \Omega$ $I_D \approx 5 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$ , $R_g = 1 \Omega$		60	90	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			22	33	
Fall Time	$t_f$			5	10	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			2.6	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				20	
Body Diode Voltage	$V_{SD}$	$I_S = 1.5 \text{ A}$		0.73	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5 \text{ A}$ , $dl/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$		26	40	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			21	32	nC
Reverse Recovery Fall Time	$t_a$			13		ns
Reverse Recovery Rise Time	$t_b$			13		

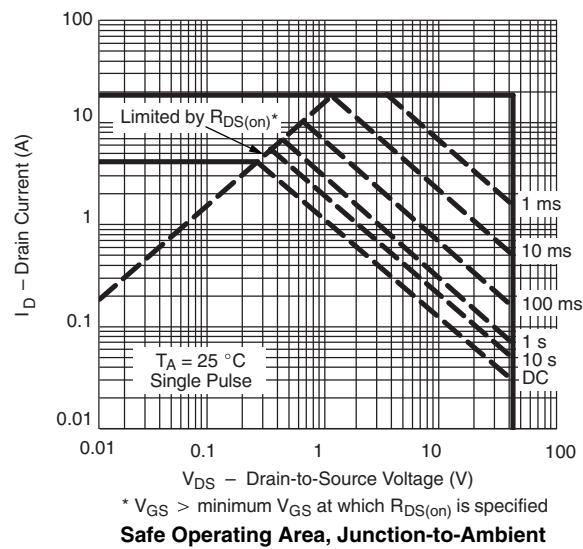
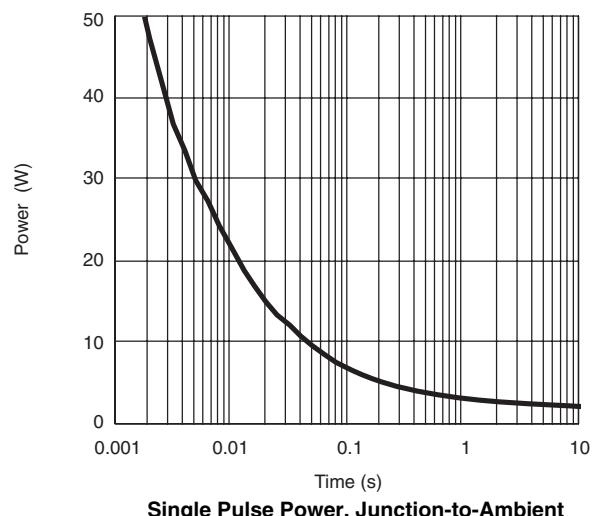
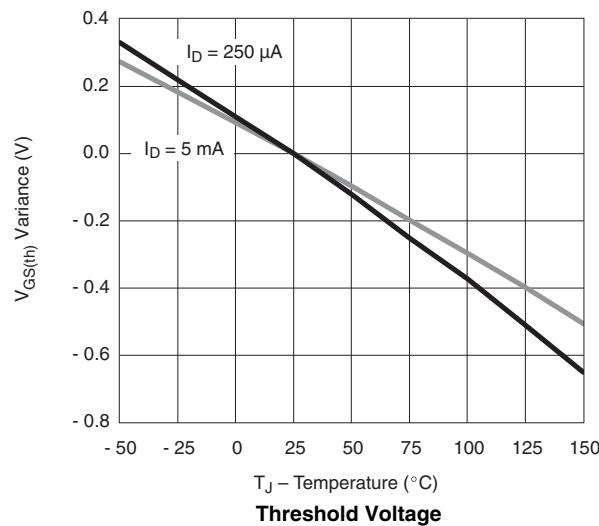
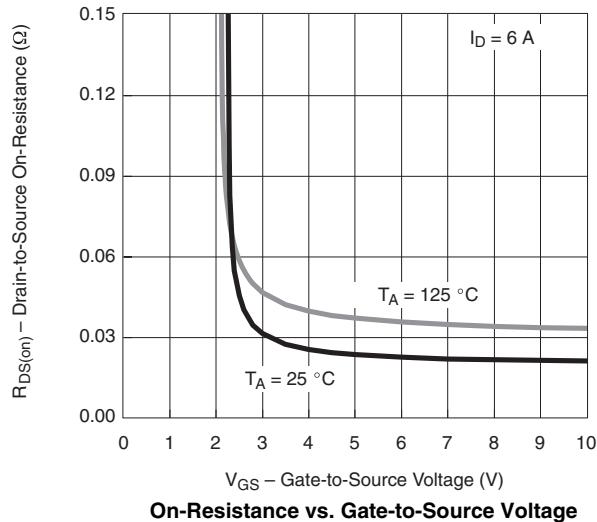
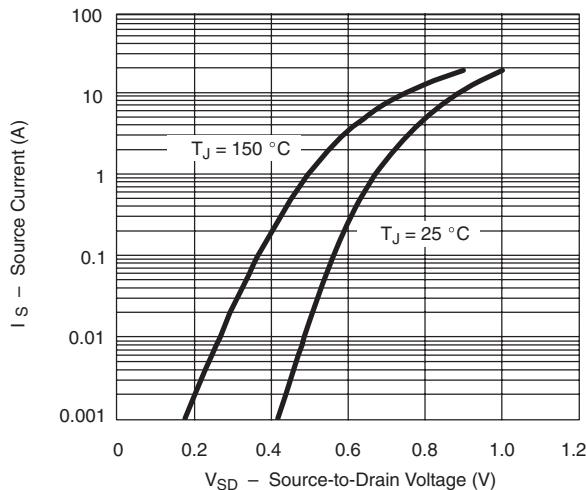
Notes:

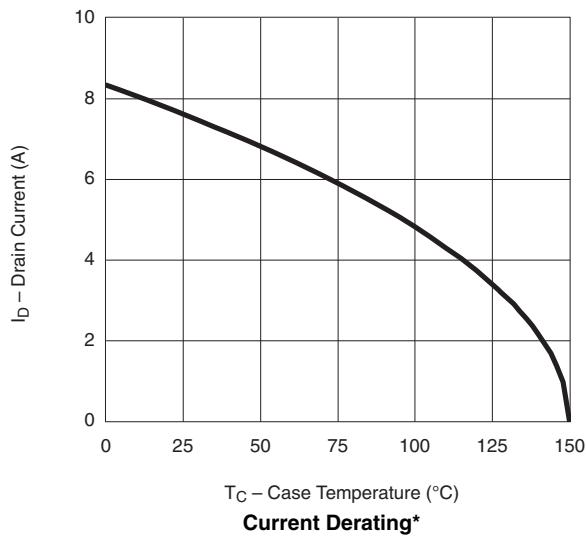
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

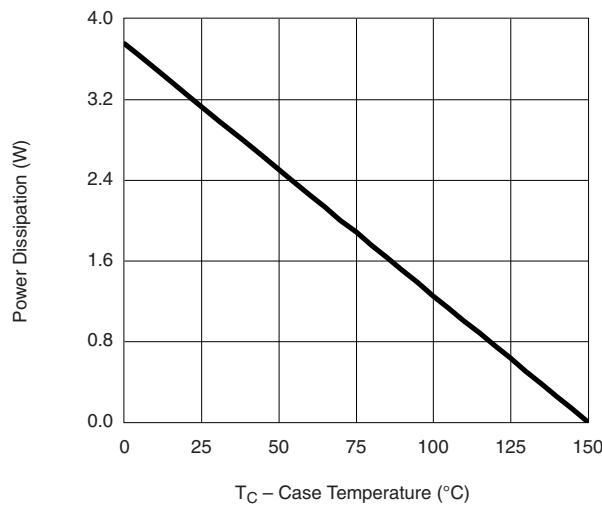
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

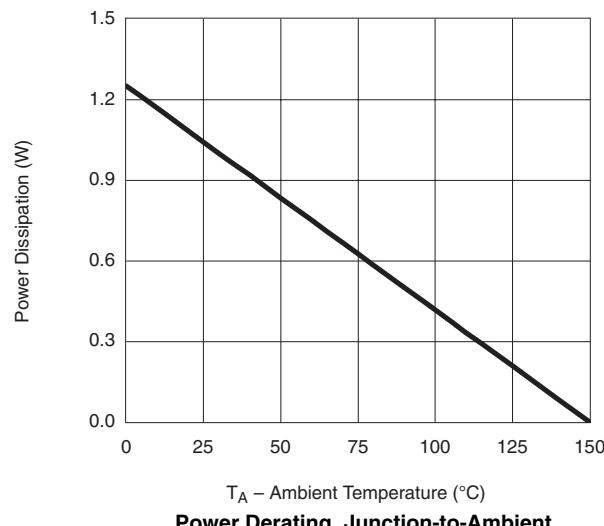
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted


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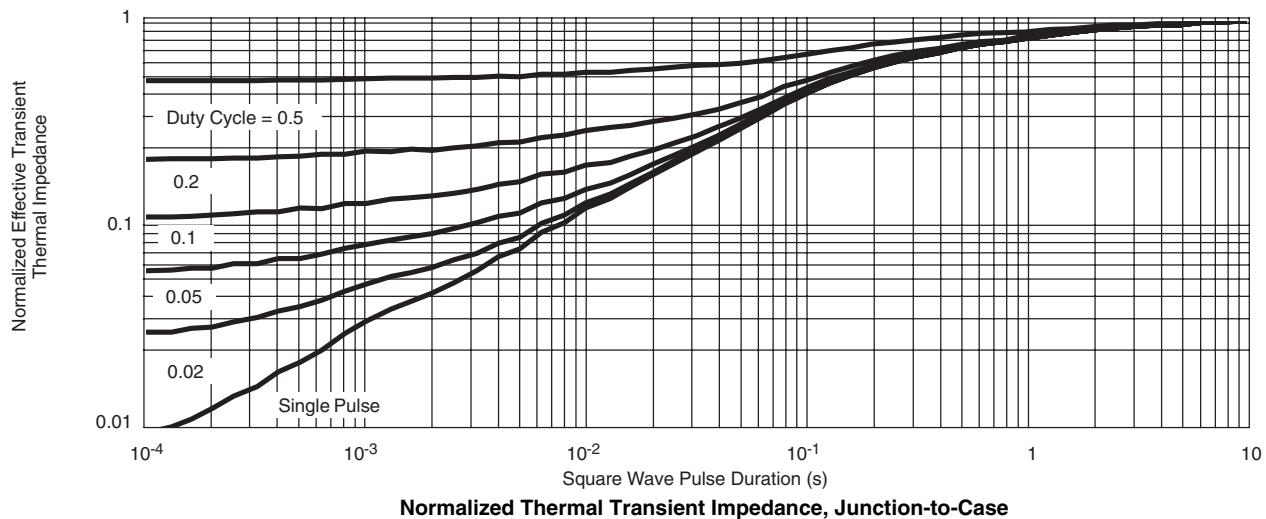
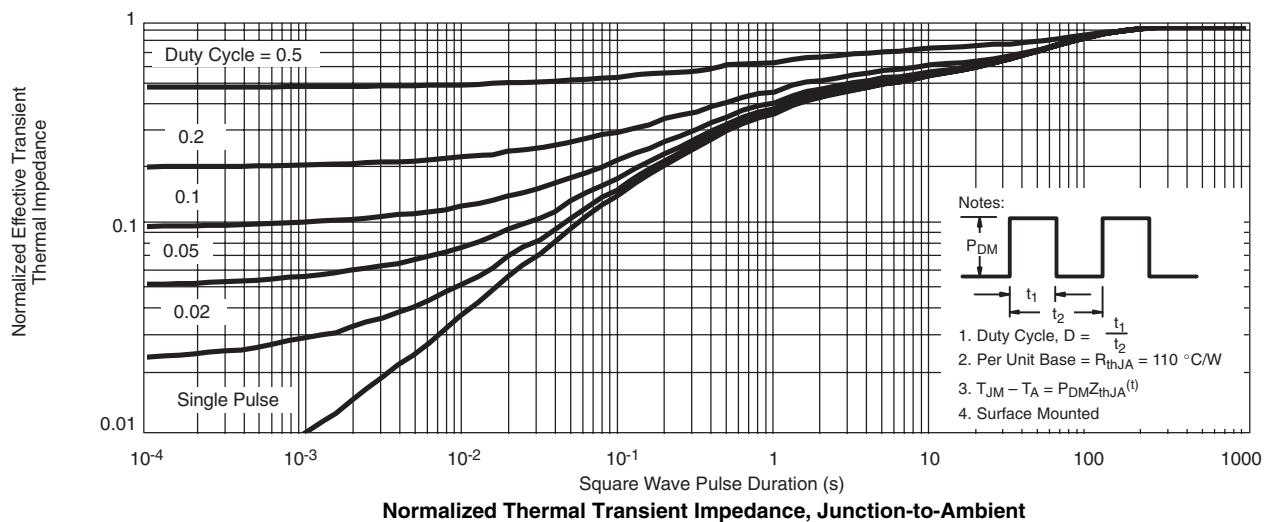
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 $T_C$  – Case Temperature (°C)

**Current Derating\***

 $T_C$  – Case Temperature (°C)

**Power Derating, Junction-to-Foot**

 $T_A$  – Ambient Temperature (°C)

**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(\max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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